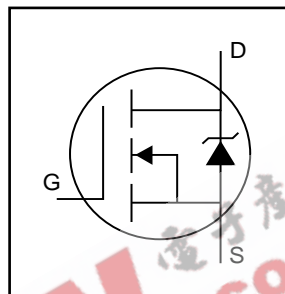


- Logic-Level Gate Drive
- Ultra Low On-Resistance
- Surface Mount (IRLR3103)
- Straight Lead (IRLU3103)
- Advanced Process Technology
- Fast Switching
- Fully Avalanche Rated

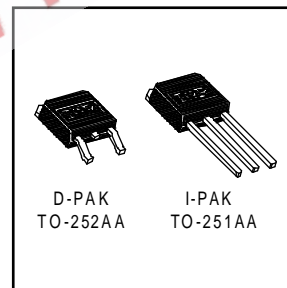


$V_{DS} = 30V$
$R_{DS(on)} = 0.019\Omega$
$I_D = 46A$ ⑤

### Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

The D-PAK is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.



### Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	46⑤	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	29⑤	
$I_{DM}$	Pulsed Drain Current ①②	220	
$P_D @ T_C = 25^\circ C$	Power Dissipation	69	W
	Linear Derating Factor	0.56	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 16$	V
$E_{AS}$	Single Pulse Avalanche Energy ②⑦	240	mJ
$I_{AR}$	Avalanche Current ①②	34	A
$E_{AR}$	Repetitive Avalanche Energy ①	6.9	mJ
dv/dt	Peak Diode Recovery dv/dt ③⑦	2.0	V/ns
$T_J$	Operating Junction and	-55 to + 150	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

### Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	1.8	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)**	—	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	—	110	

\*\* When mounted on 1" square PCB (FR-4 or G-10 Material) .

For recommended footprint and soldering techniques refer to application note #AN-994

## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.037	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	0.019	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 28A ④
		—	—	0.024		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 23A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	1.0	—	—	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Transconductance	23	—	—	S	V <sub>DS</sub> = 25V, I <sub>D</sub> = 34A ⑦
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	25	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 16V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -16V
Q <sub>g</sub>	Total Gate Charge	—	—	50	nC	I <sub>D</sub> = 34A
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	14		V <sub>DS</sub> = 24V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	—	28		V <sub>GS</sub> = 4.5V, See Fig. 6 and 13 ④ ⑦
t <sub>d(on)</sub>	Turn-On Delay Time	—	9.0	—	ns	V <sub>DD</sub> = 15V
t <sub>r</sub>	Rise Time	—	210	—		I <sub>D</sub> = 34A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	20	—		R <sub>G</sub> = 3.4Ω, V <sub>GS</sub> = 4.5V
t <sub>f</sub>	Fall Time	—	54	—		R <sub>D</sub> = 0.43Ω, See Fig. 10 ④ ⑦
L <sub>D</sub>	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact ⑥
L <sub>S</sub>	Internal Source Inductance	—	7.5	—		
C <sub>ISS</sub>	Input Capacitance	—	1600	—	pF	V <sub>GS</sub> = 0V
C <sub>OSS</sub>	Output Capacitance	—	640	—		V <sub>DS</sub> = 25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	320	—		f = 1.0MHz, See Fig. 5 ⑦

## Source-Drain Ratings and Characteristics

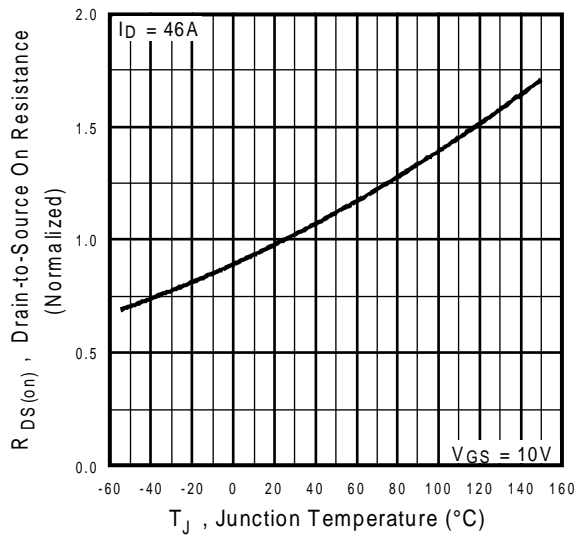
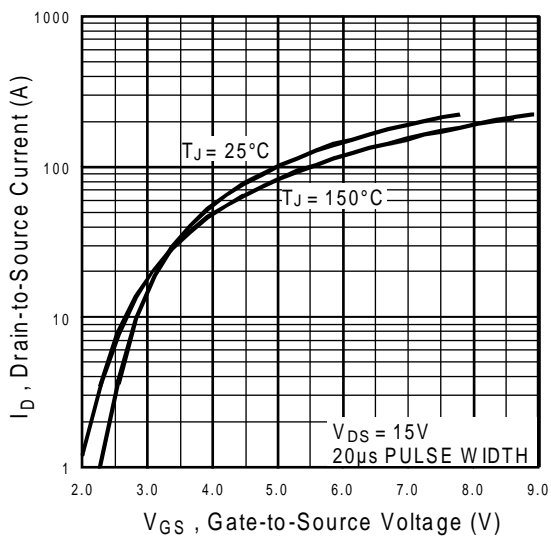
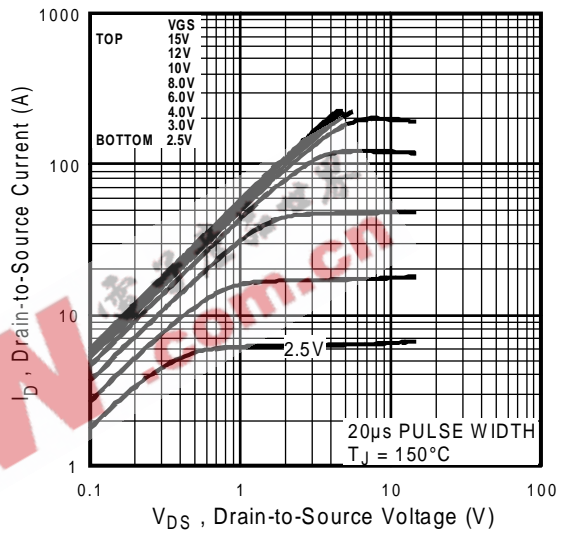
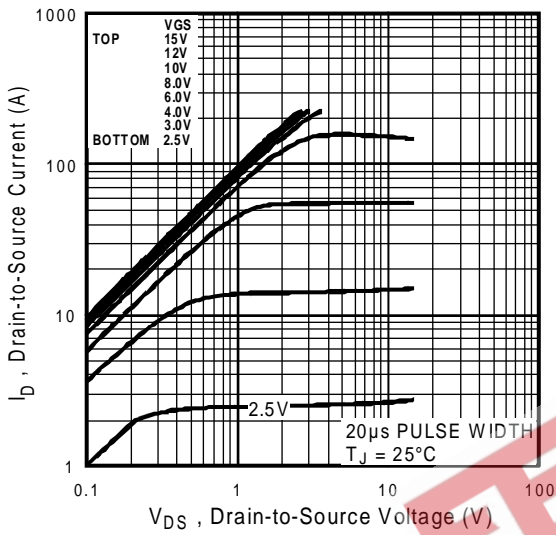
	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	46 <sup>⑤</sup>	A	MOSFET symbol showing the integral reverse p-n junction diode.
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ① ⑦	—	—	220 <sup>⑤</sup>		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 28A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	81	120	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 34A
Q <sub>rr</sub>	Reverse Recovery Charge	—	210	310	nC	di/dt = 100A/μs ④ ⑦
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

## Specification changes

Rev. #	Parameters	Old spec.	New spec.	Comments	Revision Date
1	V <sub>GS(th)</sub> (Max.)	2.5V	No spec.	Removed V <sub>GS(th)</sub> Max. Specification	5/1/96
1	V <sub>GS</sub> (Max.)	±20	±16	Decrease V <sub>GS</sub> Max. Specification	5/1/96

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )
- ② V<sub>DD</sub> = 15V, starting T<sub>J</sub> = 25°C, L = 300μH  
R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 34A. (See Figure 12)
- ③ I<sub>SD</sub> ≤ 34A, di/dt ≤ 140A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>,  
T<sub>J</sub> ≤ 150°C
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ Calculated continuous current based on maximum allowable junction temperature;  
Package limitation current = 20A.
- ⑥ This is applied for I-PAK, L<sub>S</sub> of D-PAK is measured between lead and center of  
die contact
- ⑦ Uses IRL3103 data and test conditions.



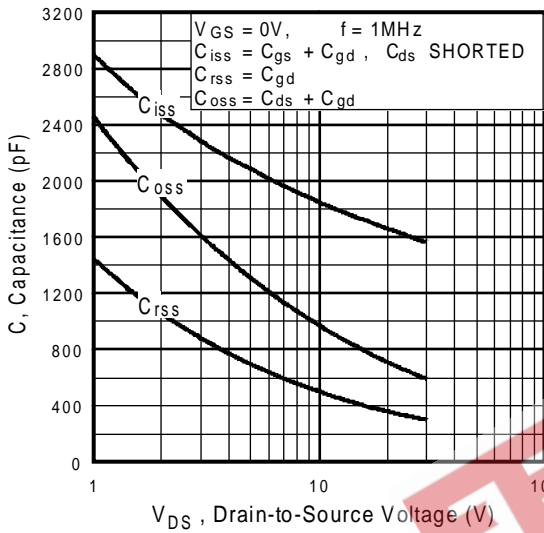


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

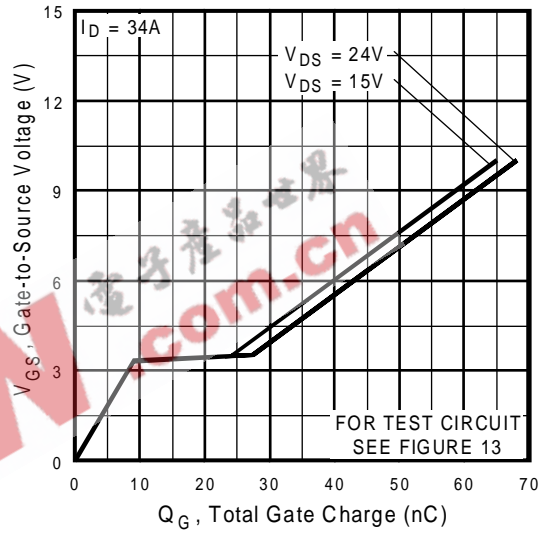


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

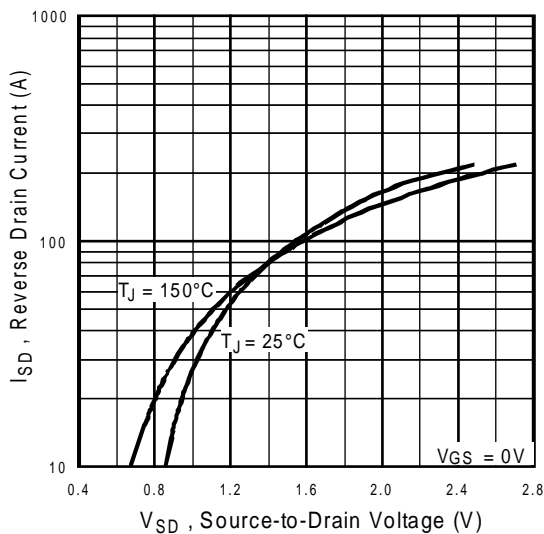


Fig 7. Typical Source-Drain Diode Forward Voltage

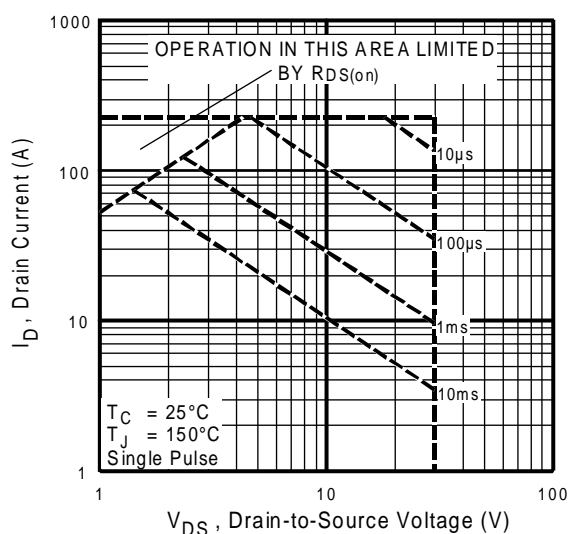


Fig 8. Maximum Safe Operating Area

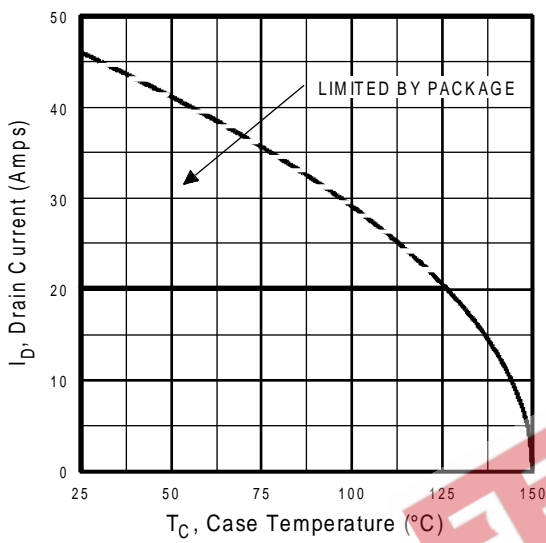


Fig 9. Maximum Drain Current Vs. Case Temperature

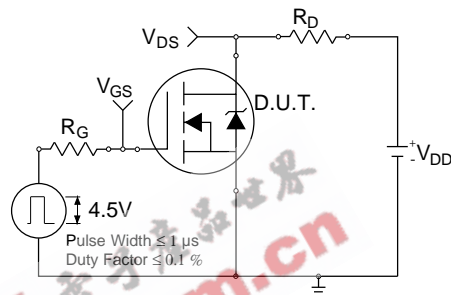


Fig 10a. Switching Time Test Circuit

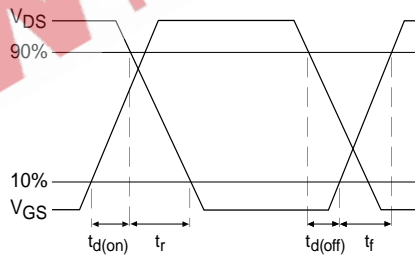


Fig 10b. Switching Time Waveforms

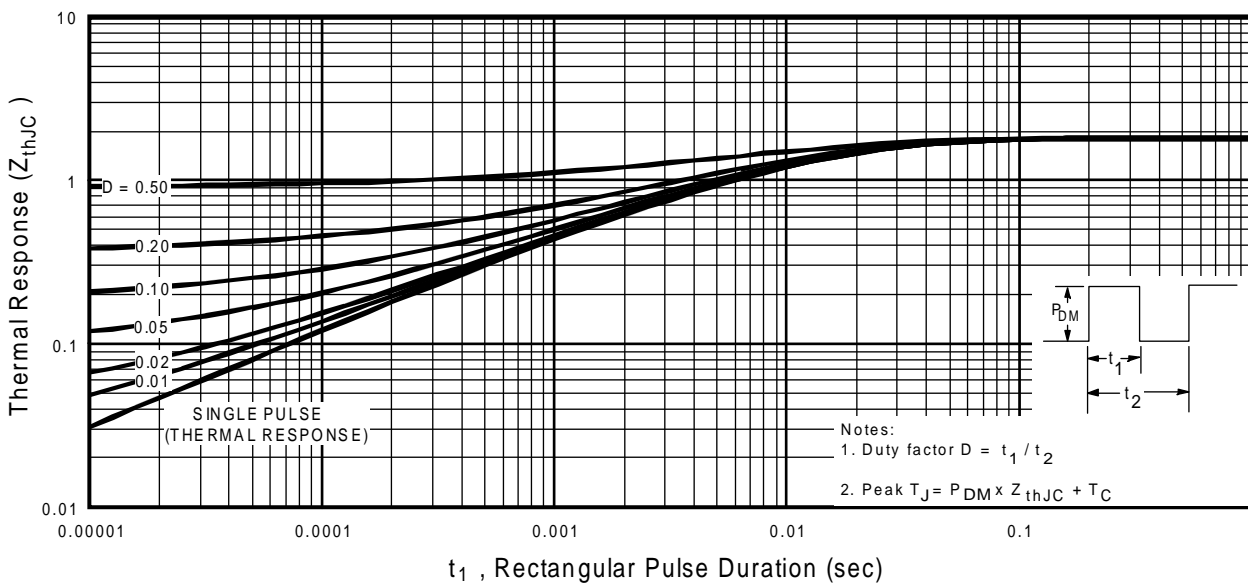


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

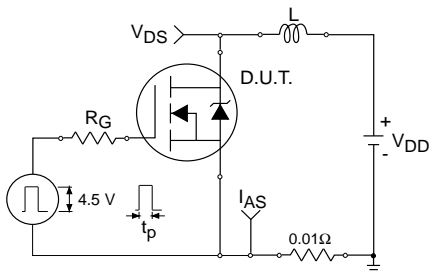


Fig 12a. Unclamped Inductive Test Circuit

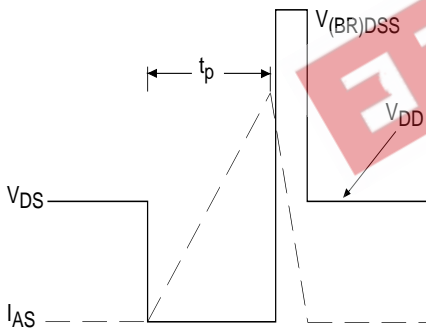


Fig 12b. Unclamped Inductive Waveforms

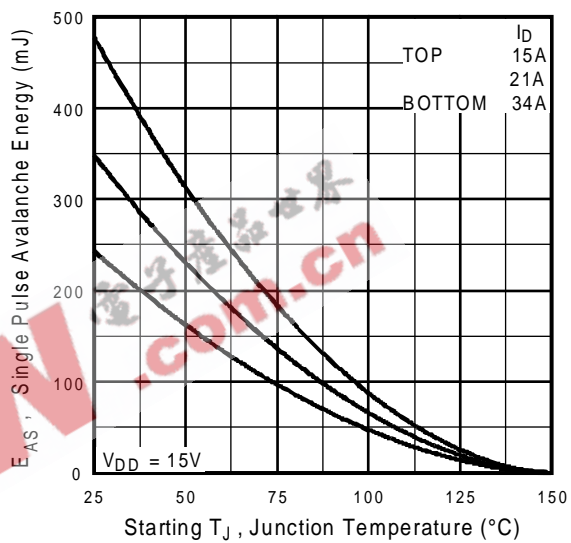


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

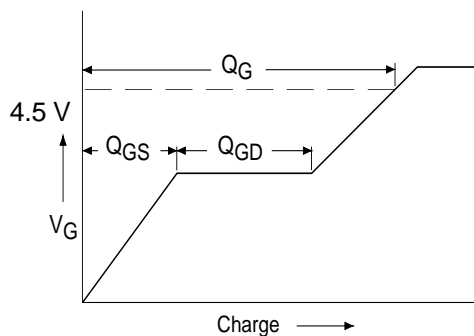


Fig 13a. Basic Gate Charge Waveform

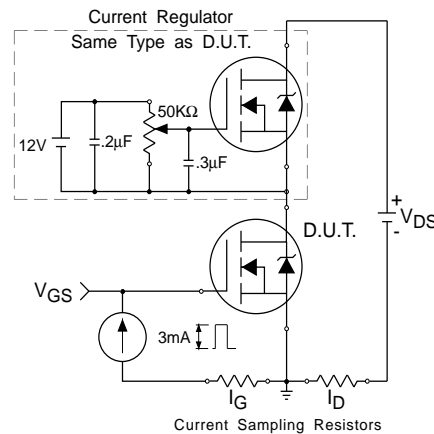
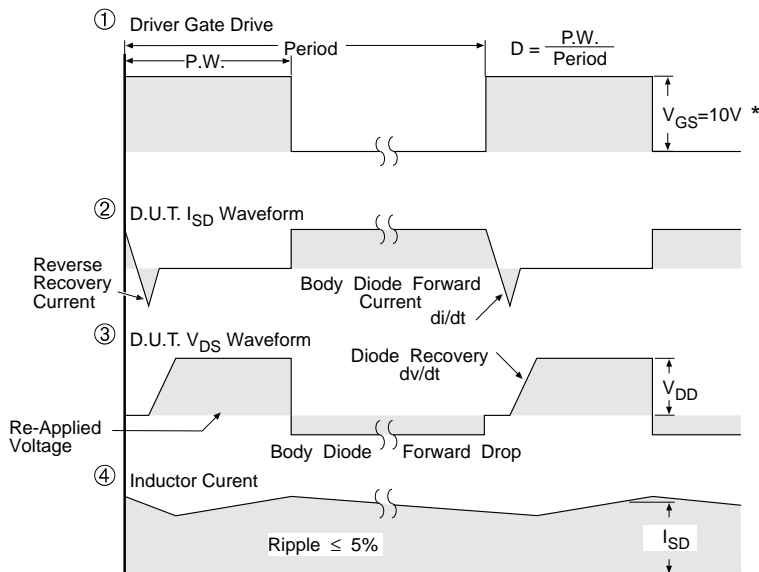
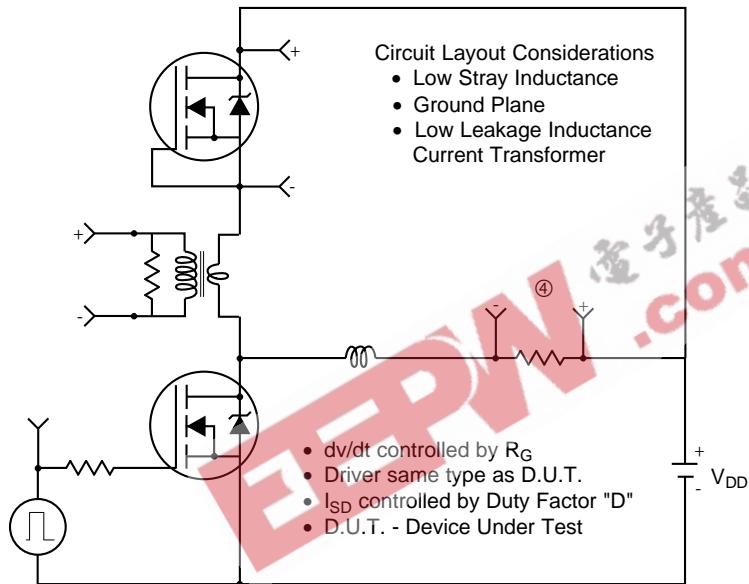


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



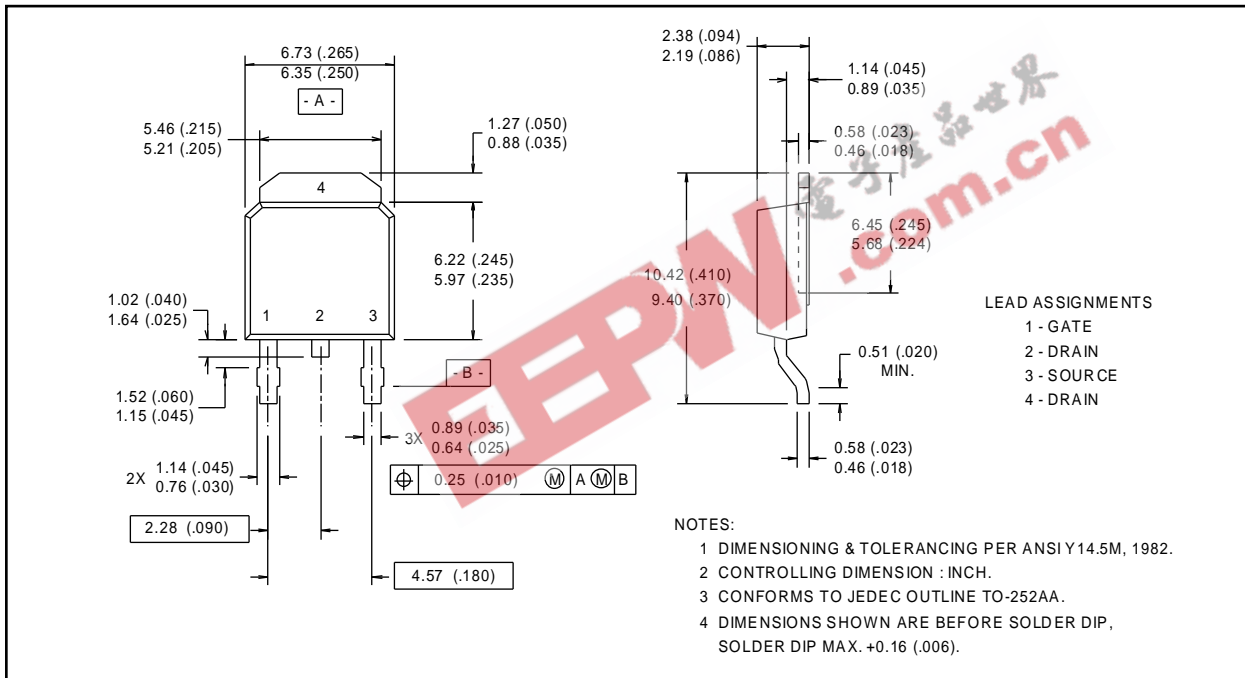
\*  $V_{GS} = 5V$  for Logic Level Devices

Fig 13. For N-Channel HEXFETS

## Package Outline

### TO-252AA Outline

Dimensions are shown in millimeters (inches)



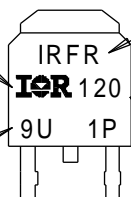
## Part Marking Information

### TO-252AA (D-PARK)

EXAMPLE : THIS IS AN IRFR120  
WITH ASSEMBLY  
LOT CODE 9U1P

INTERNATIONAL  
RECTIFIER  
LOGO

ASSEMBLY  
LOT CODE



FIRST PORTION  
OF PART NUMBER

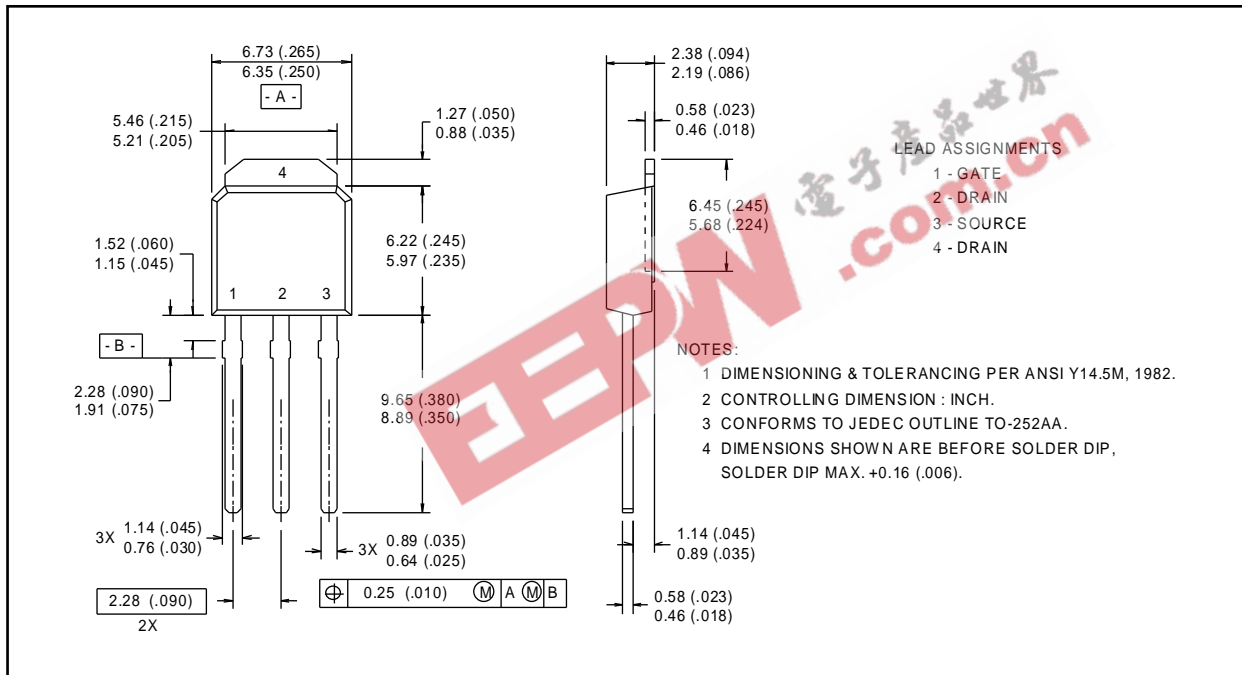
SECOND PORTION  
OF PART NUMBER



## Package Outline

### TO-251AA Outline

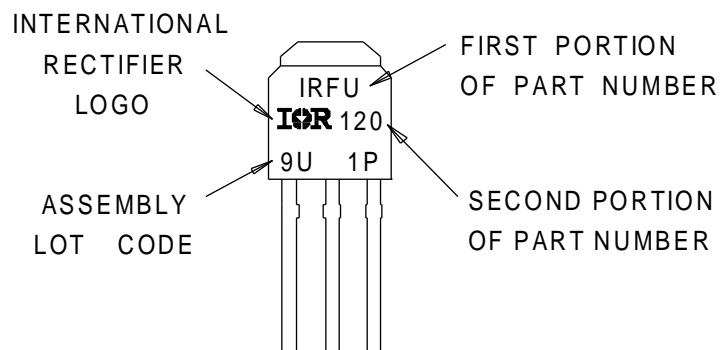
Dimensions are shown in millimeters (inches)



## Part Marking Information

### TO-251AA (I-PARK)

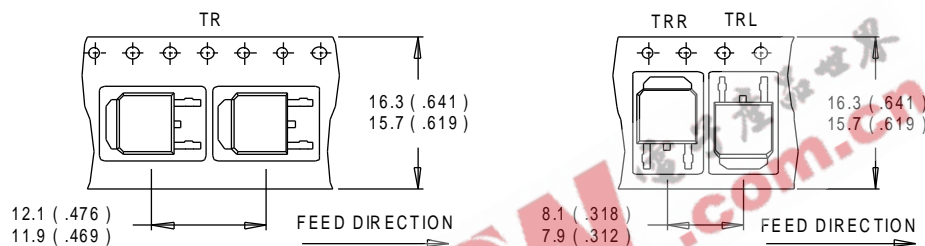
EXAMPLE : THIS IS AN IRFU120  
 WITH ASSEMBLY  
 LOT CODE 9U1P



## Tape & Reel Information

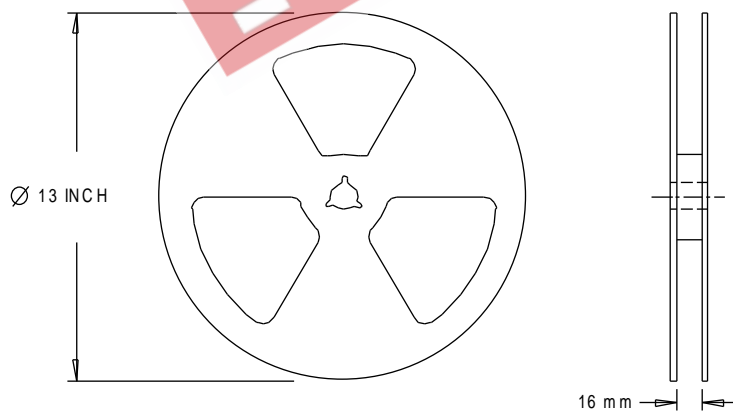
### TO-252AA

Dimensions are shown in millimeters (inches)



**NOTES :**

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



**NOTES :**

1. OUTLINE CONFORMS TO EIA-481.